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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK982

High Speed Switching Applications Analog Switch Applications Interface Applications

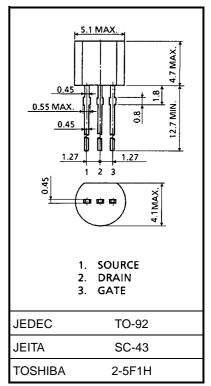
- Excellent switching times: $t_{on} = 14 \text{ ns}$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ mS} \text{ (min)}$

@ID = 50 mA

- Low on resistance: R_{DS} (ON) = 0.6 Ω (typ.) @ ID = 50 mA
- Enhancement-mode
- Complementary to 2SJ148

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC	I _D	200	mA	
	Pulse	I _{DP}	800		
Drain power dissipation		PD	400	mW	
(Ta = 25°C)		۲D	400		
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 0.21 g (typ.)

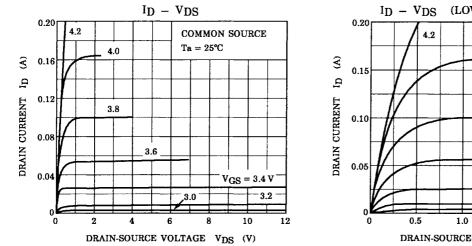
Electrical Characteristics (Ta = 25°C)

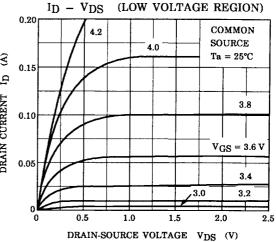
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 10~V,~V_{DS}=0$	_		±100	nA
Drain cut-off current		I _{DSS}	$V_{DS} = 60 V, V_{GS} = 0$			10	μA
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	60		_	V
Gate threshold vo	oltage	V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2		3.5	V
Forward transfer	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 50 \text{ mA}$	100		_	mS
Drain-source ON	resistance	R _{DS (ON)}	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		0.6	1.0	Ω
Drain-source ON voltage		V _{DS (ON)}	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		30	50	mV
Input capacitance		C _{iss}	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$		55	65	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$	_	13	18	pF
Output capacitance		C _{oss}	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$		40	50	pF
Switching time	Rise time	tr	$I_{D} = 100 \text{ mA}$ $I_{O} \neq V_{IN} \neq V_{OUT}$ $V_{O} \neq V_{OUT} \neq V_{OUT}$ $V_{DD} \Rightarrow 30 \text{ V}$ $V_{IN}; t_{r}, t_{f} < 5 \text{ ns}$ $D.U \leq 1\% (Z_{out} = 50 \Omega)$	_	8	_	- ns
	Turn-on time	t _{on}		_	14	_	
	Fall time	t _f		_	35	_	
	Turn-off Time	t _{off}		—	75	—	

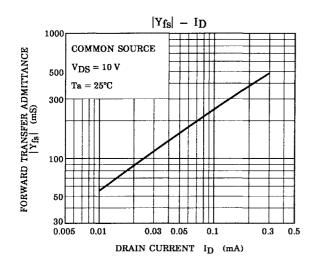
Note: This transistor is the electrostatic sensitive device.

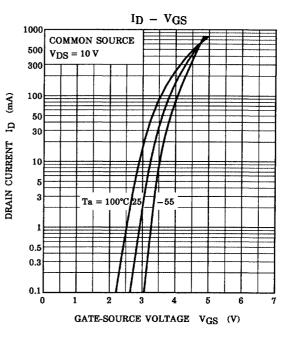
Please handle with caution.

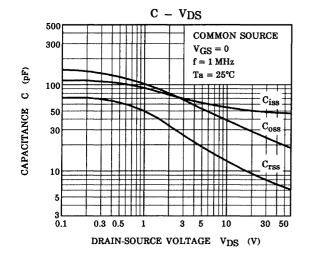
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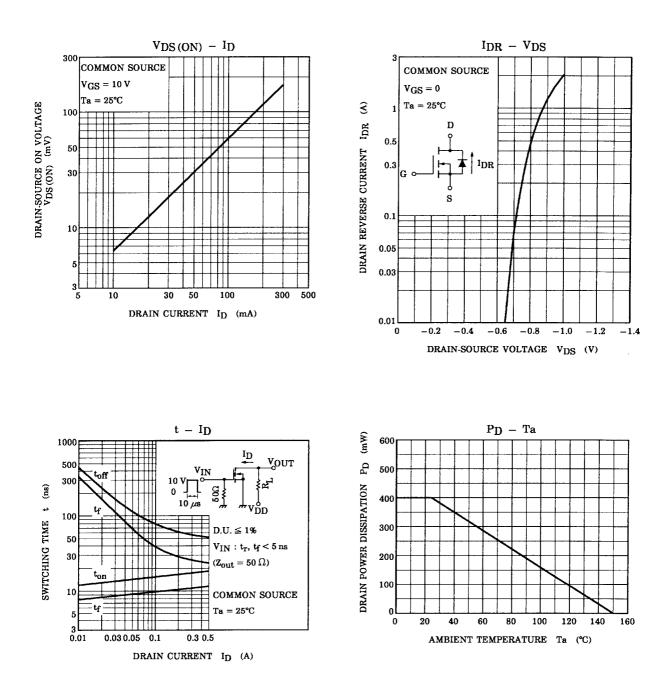








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